

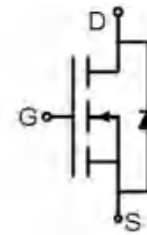
AP30H80Q

N-Channel Enhancement Mosfet



Feature

- 30V,80A
 $R_{DS(ON)} < 4.8\text{ m}\Omega @ V_{GS}=10\text{V TYP:}4.1\text{ m}\Omega$
 $R_{DS(ON)} < 9.5\text{ m}\Omega @ V_{GS}=4.5\text{V TYP:}7.2\text{ m}\Omega$
- Advanced Trench Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



Schematic Diagram

Application

- PWM applications
- Load Switch
- Power management



Marking and pin Assignment

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
30H80Q	AP30H80Q	PDFN3X3	13 inch	-	5000

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_c = 25^\circ\text{C}$)	I_D	80	A
Continuous Drain Current ($T_c = 100^\circ\text{C}$)	I_D	56	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	320	A
Single Pulsed Avalanche Energy ⁽²⁾	E_{AS}	56	mJ
Power Dissipation	P_D	46	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	2.72	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	30	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =30V, V _{GS} = 0V	-	-	1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±20V,V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage ⁽³⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.5	2.5	V
Drain-source on-resistance ⁽³⁾	R _{DS(on)}	V _{GS} =10V, I _D =30A	-	4.1	4.8	mΩ
		V _{GS} =4.5V, I _D =20A	-	7.2	9.5	
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f =1MHz	-	1614	-	pF
Output Capacitance	C _{oss}		-	245	-	
Reverse Transfer Capacitance	C _{rss}		-	215	-	
Switching characteristics						
Turn-on delay time	t _{d(on)}	V _{DD} =15V, I _D =30A, V _{GS} =10V, R _G =3Ω	-	7.5	-	ns
Turn-on rise time	t _r		-	14.5	-	
Turn-off delay time	t _{d(off)}		-	35.2	-	
Turn-off fall time	t _f		-	9.6	-	
Total Gate Charge	Qg	VDS=15V, ID=30A, VGS=10V	-	33.7	-	nC
Gate-Source Charge	Qgs		-	8.5	-	
Gate-Drain Charge	Qgd		-	7.5	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V _{DS}	V _{GS} =0V, I _S =1A	-	-	1.2	V
Diode Forward current ⁽⁴⁾	I _S		-	-	70	A

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. EAS Condition: $T_J = 25^{\circ}\text{C}, V_{DD} = 15V, R_G = 25\Omega, L = 0.5mH, I_{AS} = 15A$
3. Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
4. Surface Mounted on FR4 Board, $t \leq 10$ sec

Test Circuit

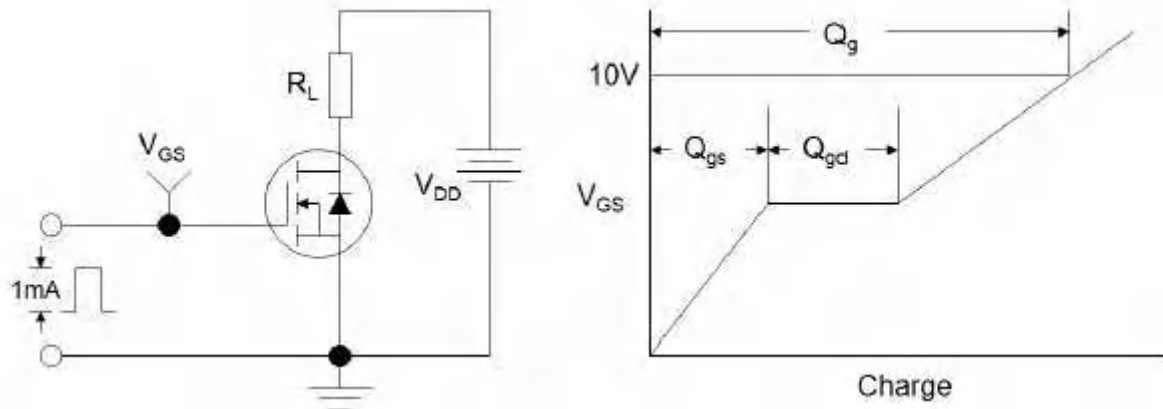


Figure1:Gate Charge Test Circuit & Waveform

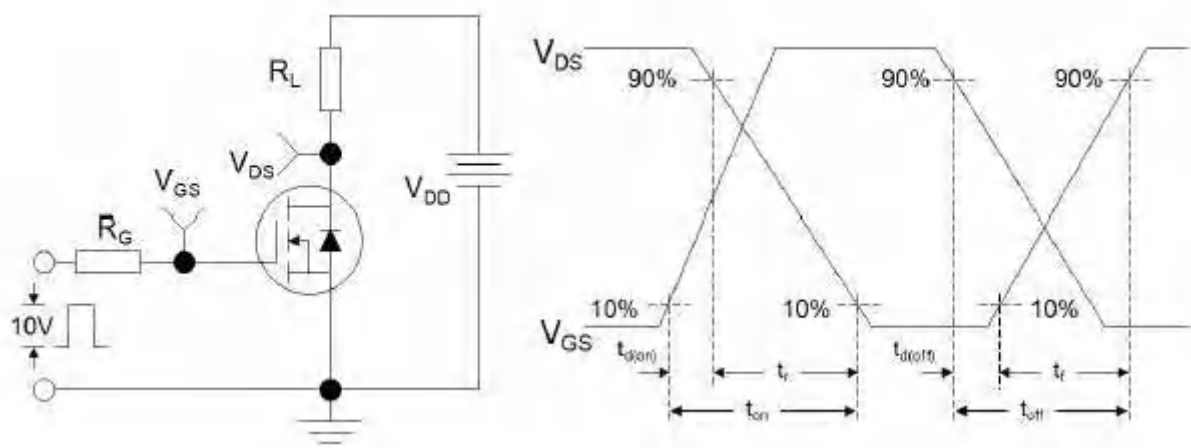


Figure 2: Resistive Switching Test Circuit & Waveforms

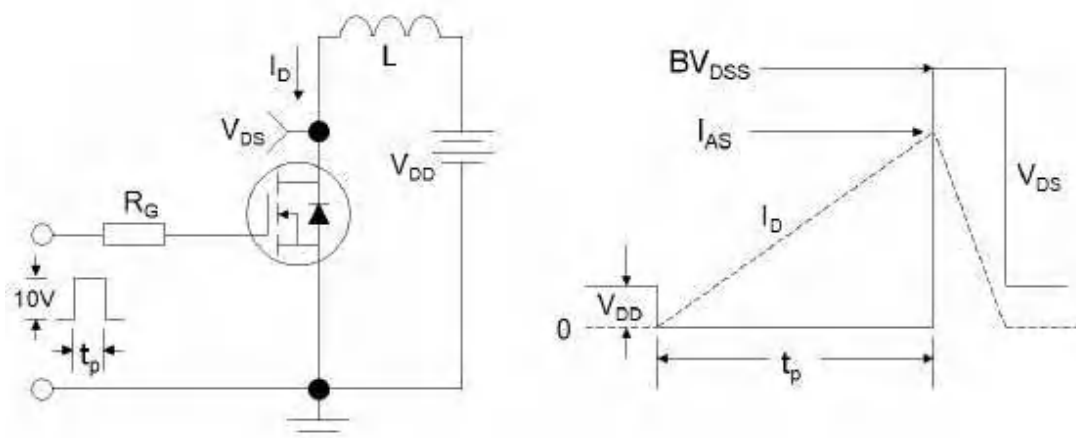


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

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Typical Performance Characteristics

Figure1: Output Characteristics

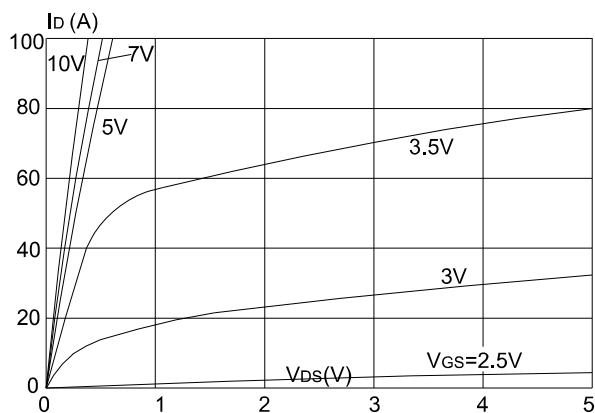


Figure 2: Typical Transfer Characteristics

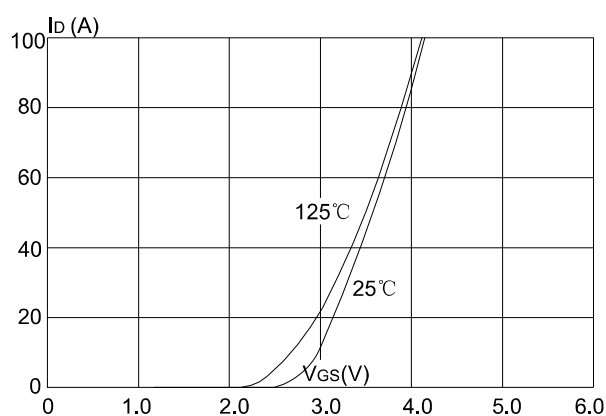


Figure 3: On-resistance vs. Drain Current

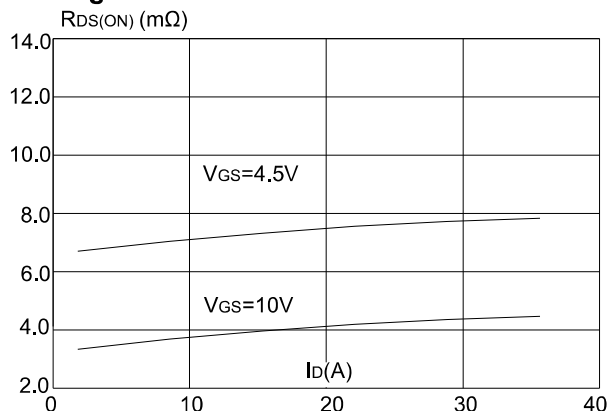


Figure 4: Body Diode Characteristics

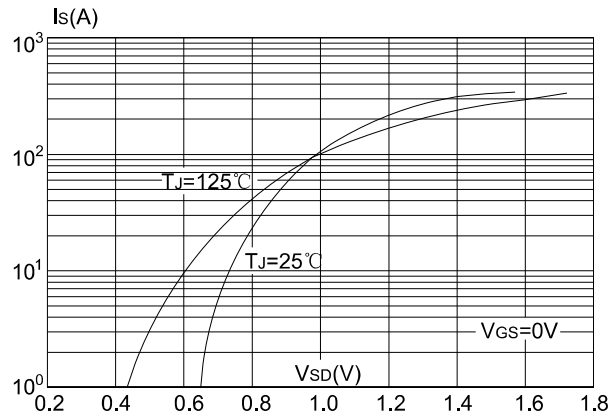


Figure 5: Gate Charge Characteristics

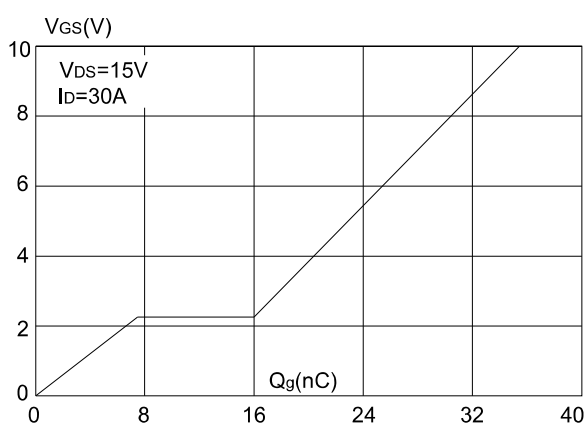
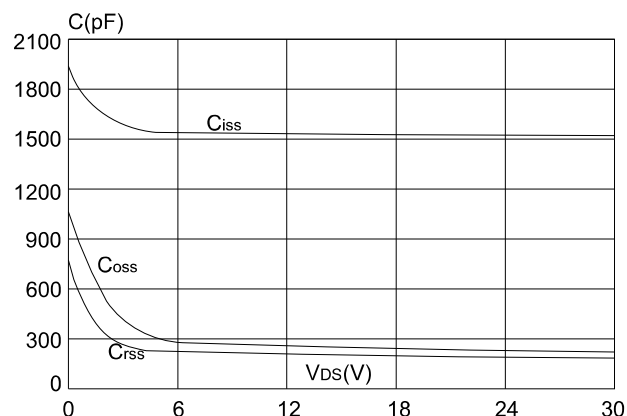


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

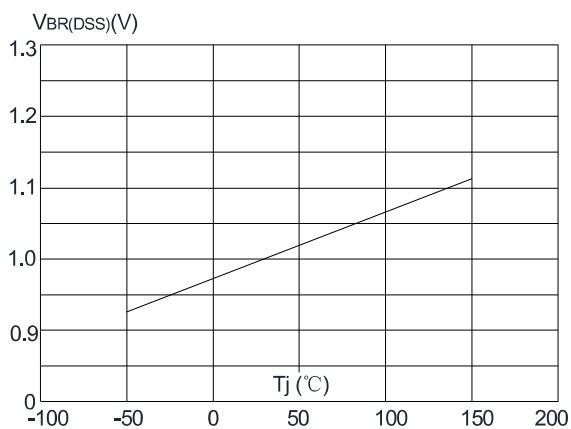


Figure 8: Normalized on Resistance vs. Junction Temperature

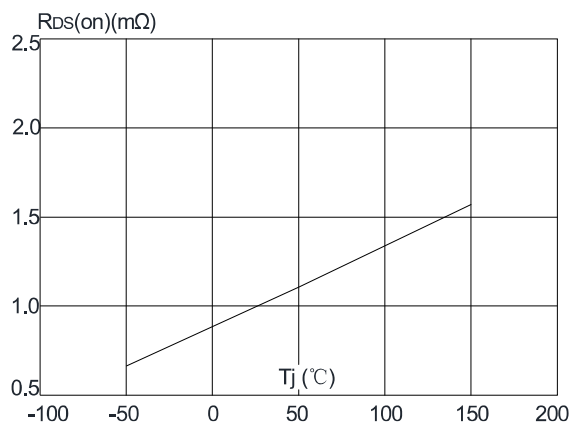


Figure 9: Maximum Safe Operating Area

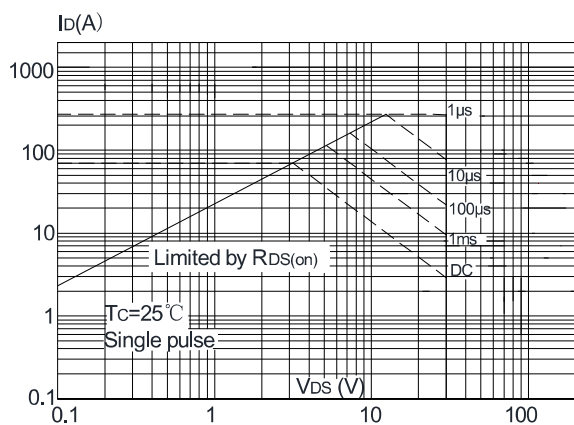


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

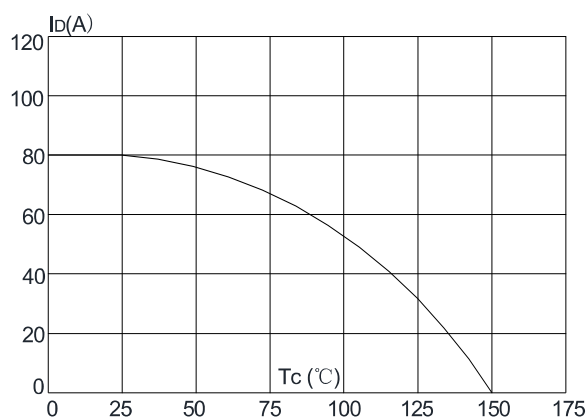
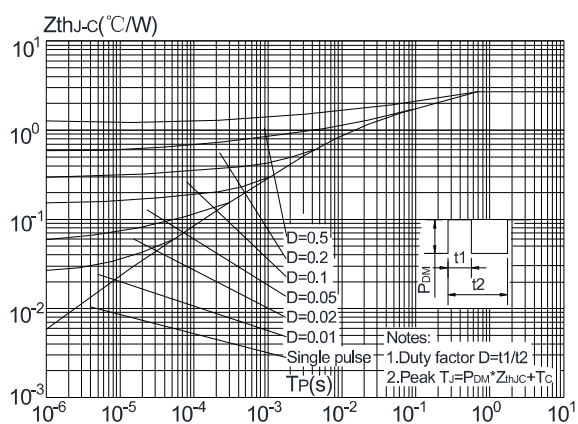
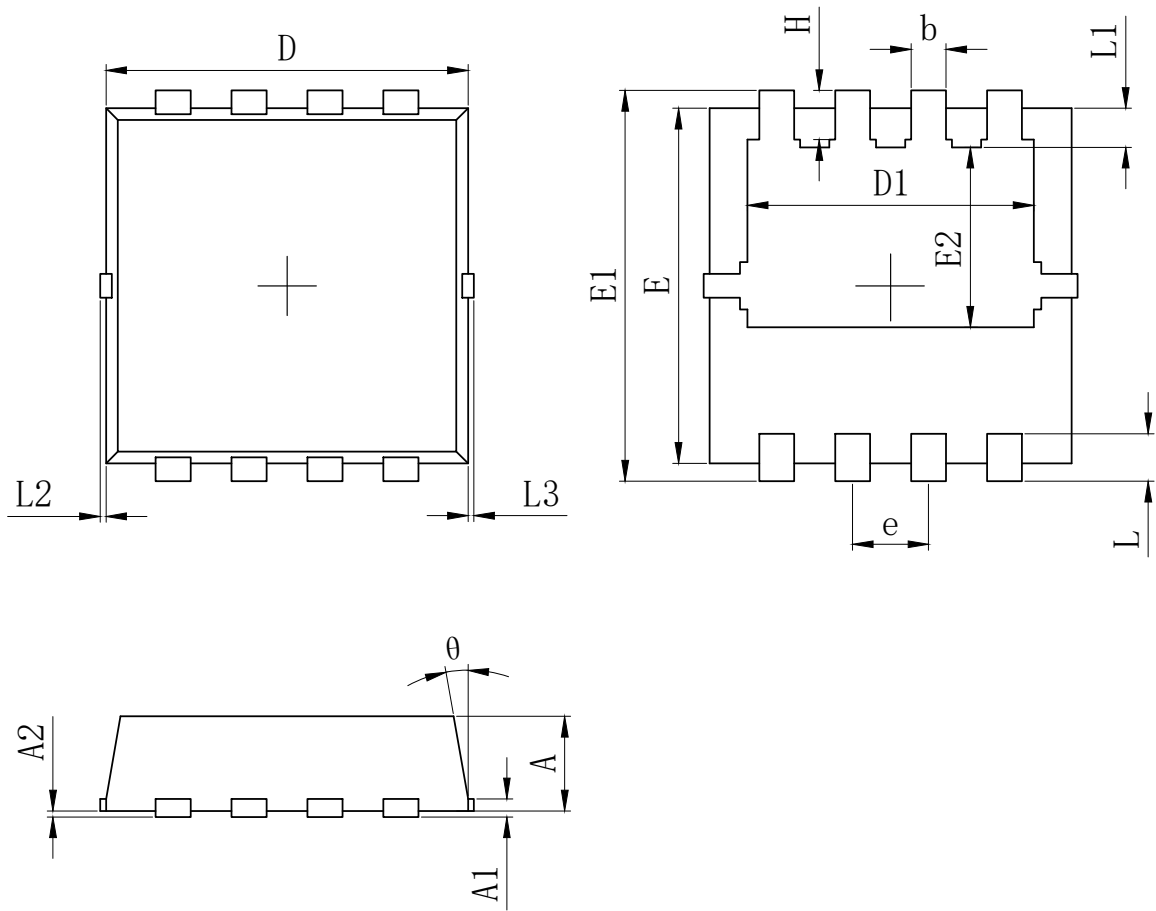


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Package Mechanical Data



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.700	0.800	0.900
A1	0.152 REF.		
A2	0~0.05		
D	3.000	3.100	3.200
D1	2.300	2.450	2.600
E	2.900	3.000	3.100
E1	3.150	3.300	3.450
E2	1.320	1.520	1.720
b	0.200	0.300	0.400
e	0.550	0.650	0.750
L	0.300	0.400	0.500
L1	0.180	0.330	0.480
L2	0~0.100		
L3	0~0.100		
H	0.315	0.415	0.515
θ	8°	10°	12°